

Panasonic

Strike a balance between high breakdown voltage and high cut-off frequency.

High breakdown voltage SiGe HBT for general RF use

Overview

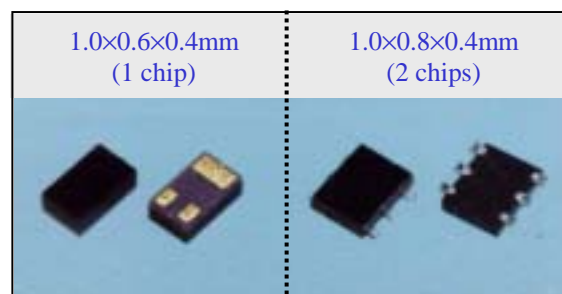
Excellent high-frequency performance and high breakdown voltage have been achieved by using the 0.25 μ m SiGe HBT. The products are suitable for VCO oscillator/buffer amplifier, TV tuner LNA and other RF applications, where improved electrical properties such as power consumption, noise figures and gain are desired. In addition, the compact body can drastically reduce the size of a handset or instrument.

Features

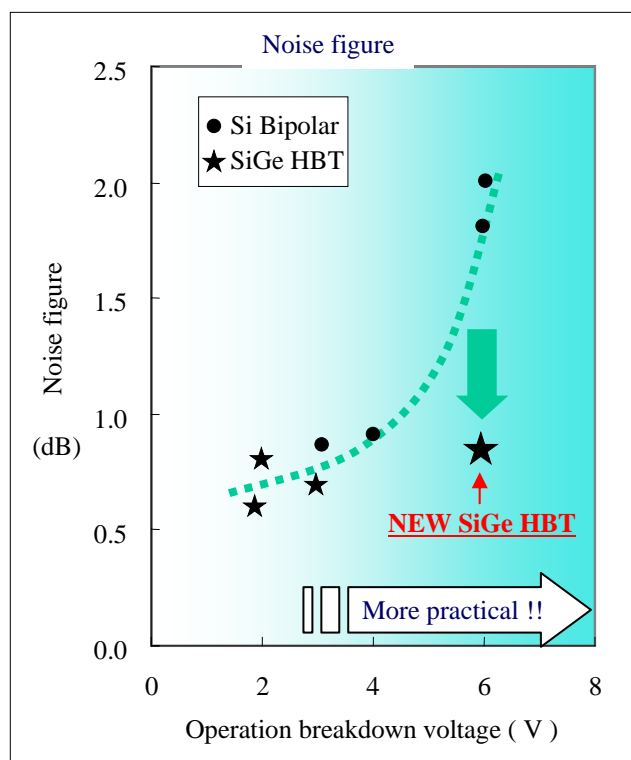
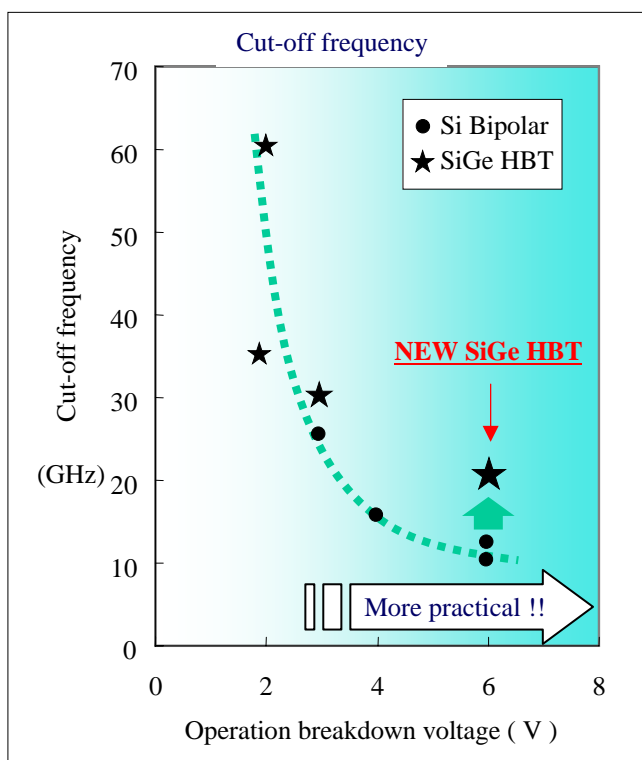
- Cut-off frequency $f_T = 20$ GHz, operation breakdown voltage $BV_{ce-on} = 6$ V, collector output capacitance = half of conventional products.
- Noise figure $NF = 0.9$ dB, power gain $PG = 16$ dB at frequency of 1 GHz.
- Ultra-small packages of ML3-N2 (1.0 \times 0.6 \times 0.4mm)/SSSMini6-F1 (1.0 \times 0.8 \times 0.4mm).

Applications

- VCO for cellular phones, PHS, wireless LANs, etc.
- LNA for cellular phones, tuners, etc.



--- Operation breakdown voltage vs cut-off frequency/noise figure ---



Products and specifications are subject to change without notice. Please ask for the latest Product Standards to guarantee the satisfaction of your product requirements.

Semiconductor Company, Matsushita Electric Industrial Co., Ltd.

■ SiGe HBT Lineup

Item \ Part No.	MSG33001	MSG33002	MSG33003	MSG33004	MSG43001
Packages	SSSMini3-F1				ML3-N2
fT	20 GHz	20 GHz	20 GHz	20 GHz	20 GHz
BVce-on	6.0 V	6.0 V	6.0 V	6.0 V	6.0 V
Cob	0.27 pF	0.37 pF	0.47 pF	0.59 pF	0.27 pF
NF*	1.3 dB	1.3 dB	1.4 dB	1.7 dB	1.3 dB
PG*	11.0 dB	10.5 dB	9.5 dB	9.0 dB	11.0 dB

*Noise figure and power gain are measured at 2 GHz/3 V.

Item \ Part No.	MSG36A51
Packages	SSSMini6-F1

fT	20 GHz	<u>Wiring diagram</u>
BVce-on	6.0 V	
Cob	0.27 pF/0.59 pF	
NF*	1.3 dB/1.7 dB	
PG*	11.0 dB/9.0 dB	

*Noise figure and power gain are measured at 2 GHz/3 V.

■ Package Information

